

60V PNP SMALL SIGNAL TRANSISTOR IN SOT323

Features

- $BV_{CEO} > -60V$
- I_C = -600mA Collector Current
- **Epitaxial Planar Die Construction**
- Ultra-Small Surface Mount Package
- Complementary NPN Type: MMST2222A
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

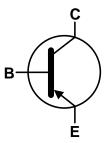
Mechanical Data

- Case: SOT323
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208@3
- Weight: 0.006 grams (Approximate)

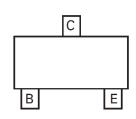




Top View



Device Symbol



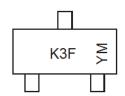
Pin-out Top View

Ordering Information (Notes 4 & 5)

Product	Status	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MMST2907A-7-F	NRND	AEC-Q101	K3F	7	8	3,000
MMST2907A-7	Active	AEC-Q101	K3F	7	8	3,000
MMST2907AQ-7	Active	Automotive	K3F	7	8	3,000

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. Notes:
 - 2. See http://www.diodes.com/quality/lead free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.
 - 5. NRND = Not Recommended for New Design. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



K3F = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: A = 2013) M or \overline{M} = Month (ex: 9 = September)

Date Code Key

Year	201	0	2011	2012	2013	2014	2015	201	6 20)17	2018	2019	2020
Code	Х		Υ	Z	Α	В	С	D		E	F	G	Н
Mont	h	Ja	n Fel	o Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	•	1	2	3	4	5	6	7	8	9	0	N	D



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-60	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current	I _C	-600	mA

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P _D	200	mW
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	625	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

Thermal Characteristics and Derating Information

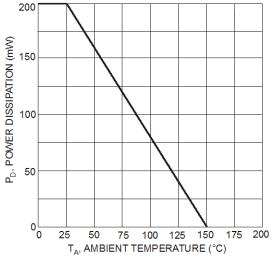


Fig. 1 Max Power Dissipation vs. Ambient Temperature

^{6.} For a device mounted with the collector lead on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

^{7.} Refer to JEDEC specification JESD22-A114 and JESD22-A115.



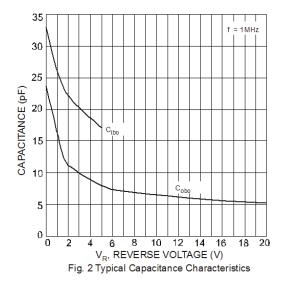
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

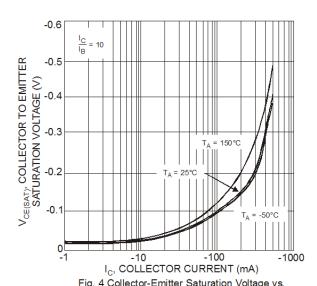
Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)					
Collector-Base Breakdown Voltage	BV _{CBO}	-60	—	V	$I_C = -10\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	BV _{CEO}	-60		V	$I_C = -10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV _{EBO}	-5	_	V	$I_E = -10\mu A, I_C = 0$
Collector Base Cutoff Current	I _{CBO}	_	-10	nΑ μΑ	V _{CB} = -50V, I _E = 0 V _{CB} = -50V, I _E = 0, T _A = +125°C
Collector Cutoff Current	I _{CEX}	_	-50	nA	$V_{CE} = -30V, V_{EB(OF F)} = -0.5V$
Base Cutoff Current	I _{BL}	_	-50	nA	$V_{CE} = -30V, V_{EB(OFF)} = -0.5V$
ON CHARACTERISTICS (Note 8)					
DC Current Gain	h _{FE}	75 100 100 100 50		_	$I_{C} = -100\mu A, \ V_{CE} = -10V$ $I_{C} = -1mA, \ V_{CE} = -10V$ $I_{C} = -10mA, \ V_{CE} = -10V$ $I_{C} = -150mA, \ V_{CE} = -10V$ $I_{C} = -500mA, \ V_{CE} = -10V$
Collector-Emitter Saturation Voltage	V _{CE(sat)}	_	-0.4 -1.6	V	$I_C = -150 \text{mA}, I_B = -15 \text{mA}$ $I_C = -500 \text{mA}, I_B = -50 \text{mA}$
Base-Emitter Saturation Voltage	V _{BE(sat)}		1.3 2.6	V	$I_C = -150 \text{mA}, I_B = -15 \text{mA}$ $I_C = -500 \text{mA}, I_B = -50 \text{mA}$
SMALL SIGNAL CHARACTERISTICS				•	
Output Capacitance	C _{obo}		8	рF	$V_{CB} = -10V$, $f = 1.0MHz$, $I_E = 0$
Input Capacitance	C _{ibo}		30	pF	$V_{EB} = -2V$, $f = 1.0MHz$, $I_{C} = 0$
Current Gain-Bandwidth Product	f⊤	200	_	MHz	$V_{CE} = -20V$, $I_{C} = -50mA$, $f = 100MHz$
SWITCHING CHARACTERISTICS					
Turn-On Time	ton	_	45	ns	V _{CC} = -30V, I _C = -150mA,
Delay Time	t _d	_	10	ns	$V_{CC} = -30V, I_{C} = -150IIIA,$ $I_{B1} = -15mA$
Rise Time	t _r	_	40	ns	IBI - TOHIA
Turn-Off Time	t _{off}	_	100	ns	\\\a= 6\\ \ \ \ \ \ \ \ \ \ \ \ \ \
Storage Time	ts	_	80	ns	$V_{CC} = -6V, I_C = -150mA,$ $I_{B1} = I_{B2} = -15mA$
Fall Time	t _f	_	30	ns	IB1 - IB2 = - IOIIIA

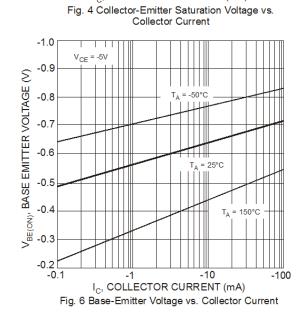
Note: 8. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)







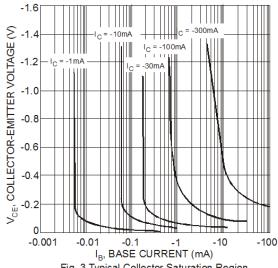


Fig. 3 Typical Collector Saturation Region

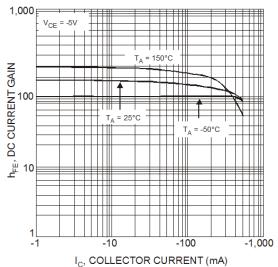


Fig. 5 DC Current Gain vs. Collector Current

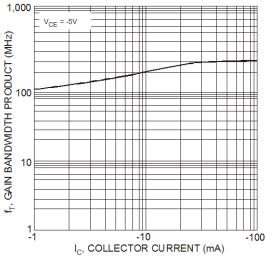
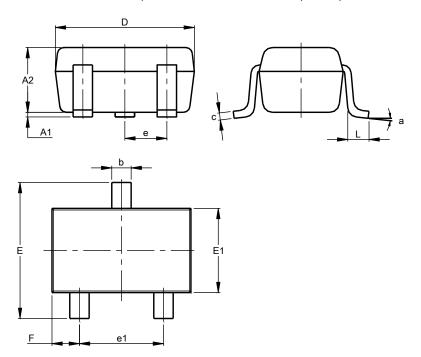


Fig. 7 Gain Bandwidth Product vs. Collector Current



Package Outline Dimensions

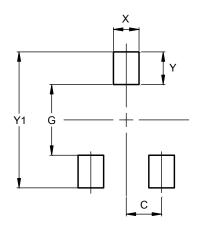
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT323						
Dim	Min	Max	Тур			
A1	0.00	0.10	0.05			
A2	0.90	1.00	0.95			
b	0.25	0.40	0.30			
С	0.10	0.18	0.11			
D	1.80	2.20	2.15			
Е	2.00	2.20	2.10			
E1	1.15	1.35	1.30			
е	().650 B	SC			
e1	1.20	1.40	1.30			
F	0.375	0.475	0.425			
L	0.25	0.40	0.30			
а	8°					
All Dimensions in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
С	0.650		
G	1.300		
Х	0.470		
Υ	0.600		
Y1	2.500		



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